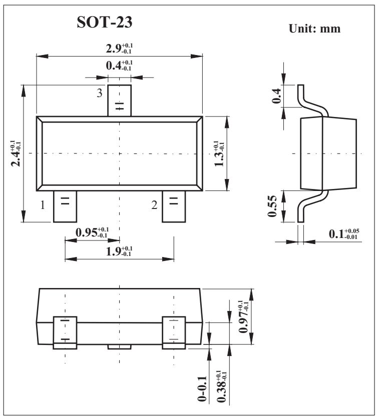
Sillicon Epitaxial Schottky Barrier Diode

1SS345



■ Features

- ● Small interterminal capacitance (C=0.45pF typ).
- ● Low forward voltage and excellent detection efficiency(V_F=0.35V max)
- ● High breakdown voltage (V_R=55V).
- ● Very small-sized package permitting the 1SS345-applied sets to be made small and slim.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	55	V
Forward Current	I_F	10	mA
Power Dissipation	P	150	mW
Junction Temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃
Reverse Burning C = 25 pF	Bo	2	erg

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	V_R	I_F = 1 mA			0.35	V
Forward Current	I_F	V_F = 1 V	10			mA
Reverse Voltage	V_R	I_R = 100 µ A	55			V
Reverse Current	I_R	V_R = 40 V			50	µ A
Interterminal Capacitance	C	V_R = 10 V, f = 1 MHz		0.45		pF

■ Marking

Marking	AH